# THE SIRIUS FACILITY : A POWERFUL TOOL FOR STUDYING RADIATION EFFECTS IN MATERIALS

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# SIRIUS geographical location



- The SIRIUS<sup>a</sup> facility is located at Laboratoire des solides irradiés (LSI<sup>b</sup>)
- The LSI is a tripartite laboratory



- $^{a}$  Irradiation platform for innovation and scientific uses
- <sup>a</sup> Irradiated solids laboratory

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## The SIRIUS facility - Production of radiation defects

SIRIUS hosts a 2.5 MeV NEC Pelletron accelerator :

- Continuous electron beam
  - 150 keV < Energy < 2.5 MeV
  - 200 nA < Current beam < 40  $\mu \rm A$
- Few mm to few cm beam size
- New installation (2013) working 24h/24, 7d/7 (300 days a year)



Electron irradiation damages in materials

2 components of damage under MeV electron irradiation

Electronic component (Electron excitation/ionization) Nuclear component (Ballistic or displacement damage)



Homogeneous effects in the Single target volume (few mm thick displa materials)

Single or double atom displacements (knock-on mechanism)

# Main research topics at SIRIUS facility

- Influence of electronic excitation in insulating materials
  - Nuclear fuel cycle (glass, concrete and clays)
  - Transient events under irradiation in components (quartz USO in space)
  - High density in optical materials (optical fiber performs)
- New materials for nuclear applications
  - Threshold displacement and migration energies from ballistic events (semiconductors, ceramics, metals)
  - Long term behavior of nuclear materials
- Irradiation as a tool for improving material properties
  - Doping effect (topological insulators, semiconductors, superconductors)
  - Radiografting (polymers, nanowires)
  - Nanostructuration induced by irradiation (plasmonic nanoparticles)

# The SIRIUS facility - Study of radiation-induced defects

### 2 beamlines hosting numerous equipment for online measurements

Beamline	Setup available	Irradiation specificities			Experiment topics examples
		Temperature (K)	Current max (µA)	Sample types	
Line 1	CRYO1	20	20	Bulks	Conductivity measurements in superconductors and topological insulators (Bi_2Te_3, Bl_2Se_3)
	CRYO2	4 ≤ T ≤ 300	2	Bulks, powders	<ul> <li>Resistivity and Hall effect measurements in topological insulators (Bi<sub>2</sub>Te<sub>3</sub>)</li> <li>Electron paramagnetic resonance<sup>*</sup></li> </ul>
	IRRAPLAST	300	10	Polymers, nanowires	<ul> <li>Irradiation in PVDF for piezoelectrical applications</li> <li>Radiografting of polymers and nanowires</li> </ul>
	LSIC*	$100 \le T \le 300$	40	Large flat samples (25 cm <sup>2</sup> max)	Electrical measurements (IV characteristics) in real-size triple junction solar cells
	in situ spectroscopy	300	40	Bulks	Photoluminescence in Sm-doped glasses, UO <sub>2</sub> discs     Time-resolved photoluminescence in halide     perovskites for photovoltaic applications     Cathodoluminescence     Raman spectroscopy
	users experiments	Depend on setup	40	Bulks, powders, liquids	<ul> <li>I-V measurements of solar cells under illumination</li> <li>Gas emitted during polymers irradiations analyzed by mass spectrometry</li> </ul>
Line 2	CIRANO	300 ≤ T ≤ 450 (670 K possible)	40	Bulks (7 cm <sup>2</sup> max), powders	<ul> <li>Defects production in nuclear glasses, Zy, Titania, UO2, SIC (<i>ex situ</i> characterization of induced point defects, threshold displacement energy calculations)</li> <li>Absorption in quartz crystal for space applications</li> </ul>

\* Under development

# SIRIUS equipments (1/6) : CRYO1

#### Set-up properties

- H<sub>2</sub> recondenser (sample chamber filled with liquid H<sub>2</sub>)
- T<sub>irr.,meas.</sub> = 20 K
- $\bullet~{\rm Cooling~power}>\!25~{\rm W}$  at 20 K
- Beam current max  $\sim 20 \ \mu A$
- *in situ* electrical measurements



#### Relevant recent works using CRYO1

- YAMASHITA et al., 2017, Fully gapped superconductivity with no sign change in the prototypical heavy-fermion CeCu<sub>2</sub>Si<sub>2</sub>, Sci. Adv., **3**:e1601667

ZHAO L. et al., 2016, Stable topological insulators achieved using high energy electron beams, Nat. Comm., 7:10957

CHO K. et al., 2017, Energy gap evolution across the superconductivity dome in single crystals of  $(Ba_{1-x}K_x)Fe_2As_2$ , Sci. Adv., **2**:e1600807

### Irradiation induced doping of topological insulators

New class of materials  $\rightarrow$  insulating in the bulk, but with gapless edge or surface states Applications in spintronic and optoelectronic



Figure: Idealized band structure for a topological insulator. The Fermi level falls within the bulk band gap which is traversed by topologically-protected surface states.



Figure: Conductivity type inversion by irradiation with 2.5 MeV electrons in Bi<sub>2</sub>Te<sub>3</sub> measured at 20 K.

#### Electron irradiation offers a path to large scale access to topological states

# SIRIUS equipments (2/6) : CRYO2

#### Set-up properties

- Two stage 4 K pulse tube cryocooler (1.5 W at 4 K)
- 3 T superconducting magnet system
- 4 K  $\leq$  T<sub>*irr.,meas.*</sub>  $\leq$  300 K
- *in situ* electrical measurements (resistivity, Hall effect)
- EPR under development

#### Recent work using CRYO2

RISCHAU C.W. et al., 2013, Doping of Bi<sub>2</sub> Te<sub>3</sub> using electron irradiation, Phys. Rev. B, 88:205207



# SIRIUS equipments (3/6) : IRRAPLAST

### Set-up properties

- $T_{\text{irradiation}} = 300 \text{ K}$
- Air or inert atmosphere (He, Ar)
- Current beam up to sev  $\mu A$
- Translation along one axis (15 cm amplitude)

### Applications

- Effect of electron irradiation on PVDF piezoelectric properties
- Radiografting of polymer films and nanowires





# Irradiation of PVDF piezoelectric polymers



# Enhancement of PVDF piezoelectrical response due to radiation-induced point defects

MELILI G. et al., 2016 How swift-heavy ions and/or e-beam irradiations act on the piezoelectric response of nanostructured polarized PVDF films, GANIL-SPIRAL2 Week

# SIRIUS equipments (4/6) : LSIC

### Set-up properties

- Large irradiation surface area :  $180 \times 130 \text{ mm}^2$
- 100 K  $\leq$  T  $_{\rm irr.,meas.}$   $\leq$  300 K
- *in situ* electrical measurements
- LED solar simulator to be implemented

### Application

Irradiation of large surface plane samples (real-size TJ solar cells)



LEFÈVRE J. et al., 2017, Dedicated tool for irradiation and electrical measurement of large surface samples on the beamline of a 2.5 MeV Pelletron electron accelerator, E3S Web of Conferences **16**:16003





### Degradation of TJ solar cells under irradiation at low T

Loss of power generation of solar cells due to radiation-induced defects at <u>low T</u> (minority carriers trapping + tunneling effect)



Figure: Light I-V characteristics of a TJ solar cell at 123 K before and after 1 MeV electron irradiation  $(1.5 \times 10^{15}/\text{cm}^2)$ 

Figure: Dark I-V characteristics (log scale) of a TJ solar cell at 123 K before and after 1 MeV electron irradiation  $(1.5 \times 10^{15}/\text{cm}^2)$ 

Image: A marked and A marked

PARK S. et al., 2017 Origin of the degradation of triple junction solar cells at low Temperature, E3S Web Conf., 16, 11th European Space Power Conference

# SIRIUS equipments (5/6): in situ spectroscopy

### Set-up properties

- T<sub>irr., meas.</sub> = 300 K
- Water-cooled sample holder
- Photoluminescence (PL), time-resolved PL, cathodoluminescence & Raman spectroscopy
- Pulse-tube cryocooler to be implemented

### Applications

- Influence of damage sublattice on PL & Raman in sintered UO<sub>2</sub> discs
- Effect of temperature on radiation-induced point defects in silica
- Mechanisms responsible for the radiodarkening of optical fiber preforms



#### Time-resolved photoluminescence (PL)

Excitation wavelength (nm)	266, 355, 532				
Pulse duration (ns)	10 (at 10 Hz)				
Detection	SR-303i Shamrock spectrometer & ICCD Istar Andor camera				
Raman spectroscopy					
Detection	Jobin Yvon HR800 spectrometer				

## Radiodarkening of optical fiber preforms

Darkening of rare-Earth doped optical fibers used for laser applications or in harsh environments



Figure: Emission of electron-irradiated Yb-doped fiber preforms samples under a 355 nm pulse laser excitation Figure: Recovery of the emission under the 355 nm laser beam during 2 hours Figure: Emission under 355 nm excitation with pulse gate delay and width (500 ns, 100  $\mu$ s) and (100  $\mu$ s, 10 ms)

Radiodarkening process of Yb-doped optical fiber preforms based on a pair association of  $Yb^{2+}$  with the so-called AlOHC point defects



OLLIER N. et al., 2016 in situ observation of the  $Yb^{2+}$  emission in the radiodarkening process of Yb-doped optical preform, Optics Letters, **41**, pp. 2025-2028

# SIRIUS equipments (6/6) : CIRANO

### Set-up properties

- $\bullet\,$  Current beam up to 40  $\mu A$
- 300 K ≤ T<sub>irr.</sub> ≤ 450 K (670 K possible)
- Irradiation in air, inert atm., or under primary vacuum
- Powder or bulk samples (few cm<sup>2</sup> max)
- Water-cooled sample holder
- Optical apertures for *in situ* UV-VIS absorption measurements



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### Frequency drifts of quartz USO used in spacecrafts



Figure: Frequency variations of the Channel 1 USO observed on-board JASON1 satellite

Figure: *in situ* absorption spectrum of an electron-irradiated quartz crystal type USO

#### Radiation-induced transient defects in the quartz crystal structure responsible for the radiation sensitivity of quartz USO

CIBIEL G. et al., 2006 Ultra stable oscillators dedicated for space applications: oscillator and quartz material behaviors vs radiation, E3S Web Conf., 16, International Frequency Control Symposium and Exposition, IEEE

# SIRIUS :

- is a platform dedicated to the production and study of electron-irradiation induced defects in materials
- hosts numerous equipment for online measurements
- welcomes an ever increasing number of international users
- is involved in a wide range of R&D topics

SIRIUS is a part of EMIR, the french network of accelerators dedicated to material irradiation...

### The EMIR federation

### Five complementary platforms :



**JANNUS-Orsay** 

Saclay

CEMHTI Orléans

### The EMIR platforms

### Main specificities of the EMIR platforms (http://emir.in2p3.fr)

Platfom	Specificities	in situ characterizations					
IONS							
<b>CEMHTI</b> (Orléans)	HIGH-ENERGY LIGHT IONSCyclotron $H \rightarrow He$ $10 - 45$ MeVVdG $H \rightarrow He$ $0.5 - 3$ MeV	<ul><li>Large range of ions</li><li>4 beam lines</li></ul>	<ul> <li>RBS</li> <li>Variable temperature Raman</li> <li>Mechanical stress</li> </ul>				
GANIL (CIMAP Caen)	$\begin{array}{c} \textit{SWIFT HEAVY IONS} \\ \text{IRRSUD} & C \! \rightarrow \! \cup  10 - 90 \text{ MeV} \\ \text{SME} & H \! \rightarrow \! \text{Bi}  0.5 - 570 \text{ keV} \end{array}$	<ul> <li>Large range of ions</li> <li>Effects dominated by electronic excitations</li> </ul>	<ul> <li>X-ray diffraction</li> <li>IR and UV-visible spectroscopies</li> <li>Gas emission</li> </ul>				
JANNUS (CSNSM Orsay)	DOUBLE BEAMS           ARAMIS         2.0 MV H→Bi         0.5 - 15 MeV           IRMA         170 kV H→Bi         0.5 - 570 keV	<ul> <li>Irradiation or implantation and TEM observation simultaneously</li> <li>100 K &lt; Tirradiation &lt; 1200 K</li> </ul>	Transmission electron microscopy     Raman and RBS spectroscopy, ERDA, NRA				
JANNUS (SRMP Saclay)	$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	<ul> <li>Irradiation and implantation simultaneously</li> <li>77 &lt; Tirradiation &lt; 800 K</li> </ul>	<ul> <li>Raman spectroscopy</li> <li>Rutherford backscattering spectrometry (RBS)</li> <li>Elastic recoil detection analysis (ERDA)</li> <li>Nuclear reaction analysis (NRA)</li> </ul>				
		ELECTRONS					
HVTEM (SRMA Saclay)	1.0 MeV	<ul> <li>Irradiation inside a high voltage TEM</li> <li>300 K &lt; Tirradiation &lt; 1000 K</li> </ul>	Imaging of structural X-ray diffraction, environmental electron microscope				
SIRIUS (LSI Palaiseau)	CONTINUOUS ELECTRON BEAM 2.5 MeV	<ul> <li>Large irradiated area</li> <li>Large energy range</li> <li>20 K &lt; Tirradiation &lt; 670 K</li> </ul>	Electrical measurements (Hall effect, resisitivity, IV characterization)     Raman spectroscopy, absorption, time-resolved PL, cathodoluminescence     Corrosion under irradiation     Electron paramagnetic resonance being developed				